QP Code: 4887

(3 Hours)

[Total Marks: 80

N.B (1) Question Nos. 1 is compulsory.

- (2) Attempt any three questions from the remaining five questions.
- (3) Figure to the right indicates full marks.
- (4) Assume suitable data whenever necessary but justify the same.
- 1 (a) Compare clipper and clamper circuit.

[5]

(b) Explain Barkhausen criteria for sustained oscillations.

[5]

(c) Compare Depletion and Enhancement type MOSFET.

[5]

- (d) Transistor is a current controlled device while FET is a voltage controlled device. Justify. [5]
- Q2 (a) Define Stability factor. Derive the equation for Stability factor. State which

biasing technique is more stable. Justify your answer.

[10]

(b) For a NPN transistor in CE mode voltage divider bias configuration determine

 V_C and V_B . Given $V_{CC} = +20V$, $V_{EE} = -20V$, $R_1 = 8.2K\Omega$, $R_2 = 2.2K\Omega$, $R_C = 2.7K\Omega$,

$$R_E = 1.8 \text{ K}\Omega$$
, $C_1 = C_2 = 10 \mu\text{F}$ and $\beta = 120$.

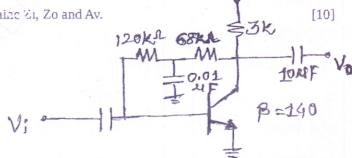
[10]

Q3 (a) Derive the equations for Av, Ai, Ri and Ro for a NPN transistor in CE mode voltage

divider bias configuration with RE unbypassed.

[10]

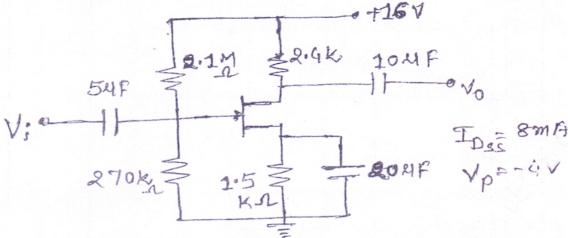
(b) For the network given below determine 21, Zo and Av.



- Q4 (a) Explain the basic operation and characteristics of n-channel enhancement type MOSFET. [10]
 - (b) Draw a neat circuit diagram of Wien bridge oscillator and derive an expression for its output frequency. [10]

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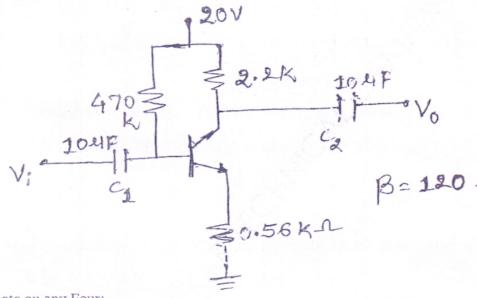
Q5.) a) Determine IDQ, VGSQ, VD & VS for the network given below:



b) Determine Zi, Zo & Av for the circuit given below.

[10]

[10]



Q6. Write short note on any Four:-

[20]

- i) Biasing of JFET for Zero temperature drift.
- ii) Energy band diagram of MOS capacitor.
- iii) Small signal equivalent circuit of CC amplifier.
- iv) Crystal oscillator
- v) DC load line & significance of Q point.

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